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SBOS878D – JULY 2017–REVISED OCTOBER 2019

# TSV91x Rail-to-Rail Input/Output, 8-MHz Operational Amplifiers

Technical

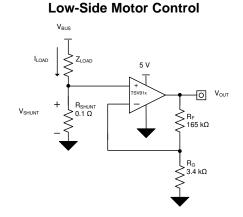
Documents

## 1 Features

- Rail-to-rail input and output
- Low noise: 18 nV/√Hz at 1 kHz
- Low power consumption: 550 µA (typical)
- High-gain bandwidth: 8 MHz
- Operating supply voltage from 2.5 V to 5.5 V
- Low input bias current: 1 pA (typical)
- Low input offset voltage: 1.5 mV (maximum)
- Low offset voltage drift: ±0.5 µV/°C (typical)
- ESD internal protection: ±4-kV human-body model (HBM)
- Extended temperature range: -40°C to 125°C

## 2 Applications

- Battery-powered applications
- Motor control
- Power modules
- HVAC: heating, ventilating, and air conditioning
- Washing machines
- Refrigerators
- Medical instrumentation
- Active filters
- Sensor signal conditioning
- Audio receiver
- Automotive infotainment



# 3 Description

Tools &

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The TSV91x family, which includes single-, dual-, and quad-channel operational amplifiers (op amps), is for specifically designed general-purpose applications. Featuring rail-to-rail input and output (RRIO) swings, wide bandwidth (8 MHz), and low offset voltage (0.3 mV, typical), this family is designed for a variety of applications that require a good balance between speed and power consumption. The op amps are unity-gain stable and feature an ultralow input bias current, which enables the family to be used in applications with high-source impedances. The low input bias current allows the devices to be used for sensor interfaces, battery-supplied and portable applications, and active filtering.

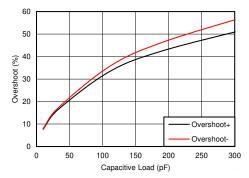
The robust design of the TSV91x provides ease-ofuse to the circuit designer. Features include a unitygain stable, integrated RFI-EMI rejection filter, no phase reversal in overdrive condition, and high electrostatic discharge (ESD) protection (4-kV HBV).

Device information '						
PART NUMBER	PACKAGE	BODY SIZE (NOM)				
TSV911	SOT-23 (5)	1.60 mm × 2.90 mm				
12/911	SC70 (5)	1.25 mm × 2.00 mm				
	SOIC (8)	3.91 mm × 4.90 mm				
TSV912	WSON (8)	2.00 mm × 2.00 mm				
	SOT-23 (8)	1.60 mm × 2.90 mm				
T0\/044	SOIC (14)	8.65 mm × 3.91 mm				
TSV914	TSSOP (14)	4.40 mm × 5.00 mm				

Device Information<sup>(1)</sup>

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### Small-Signal Overshoot vs Load Capacitance



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## **4** Revision History

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Added SOT-23 (8) (DDF) package information to data sheet	Page
Added SOT-23 (8) (DDF) package information to data sheet	1
Changes from Revision B (April 2018) to Revision C	Page
Deleted preview notations for TSV911IDBV	1

•	Added SC70 package information to Device Information table	. 1
•	Deleted package preview notation from TSV911 DBV (SOT-23) package	. 4
•	Added DCK (SC70) package information to Device Comparison Table	. 4
•	Deleted TSV911 DBV (SOT-23) package preview notation from Pin Configuration and Functions section	. 5
•	Added TSV911 DCK (SC70) package drawing and pin functions	. 5
•	Added TSV911 DBV and DCK package thermal information	. 8

## Changes from Revision A (October 2017) to Revision B

Submit Documentation Feedback

•	Changed TSV914 14-pin TSSOP package from preview to production data in Device Information table	. 1
•	Deleted package preview note from 8-pin WSON package in Device Information table	. 1
•	Deleted package preview note from PW (TSSOP) package from Device Comparison table	. 4
•	Deleted package preview note from DSG (WSON) package from Device Comparison table	. 4
•	Deleted package preview note from TSV912 DSG package pinout drawing in Pin Configuration and Functions section	. 6
•	Added DGK (VSSOP) thermal information to Thermal Information: TSV912 table	9
•	Deleted package preview note to TSV914 PW (TSSOP) package Thermal Information table	. 9
•	Added PW (TSSOP) package information to Thermal Information: TSV914 table	9
•	Changed TSV914 PW (TSSOP) junction-to-ambient thermal resistance from 135.8°C/W to 205.8°C/W	. 9
•	Changed TSV914 PW (TSSOP) junction-to-case(top) thermal resistance from 64°C/W to 106.7°C/W	. 9
•	Changed TSV914 PW (TSSOP) junction-to-board thermal resistance from 79°C/W to 133.9°C/W	. 9

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CI	hanges from Original (July 2017) to Revision A	Page
•	Changed TSV914 14-pin SOIC package from preview to production data in Device Information table	1
•	Deleted TSV911 SC70, SOT-553 and SOIC packages from Device Information table	1
•	Deleted TSV912 VSSOP packages from Device Information table	1
•	Deleted TSV911 SC70 and SOIC packages from pinout drawings and Pin Functions table	5
•	Deleted TSV912 DGK and DGS packages from pinout images Pin Functions table	6
•	Deleted package preview note from TSV914 pinout drawing and Pin Functions table	7
•	Added TSV914 Thermal Information table	9
•	Added 2017 copyright notice to Figure 35	20

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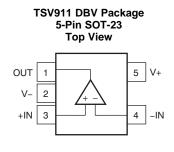
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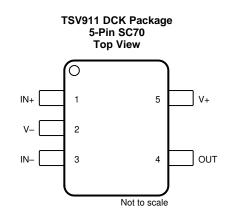
# 5 Device Comparison Table

DEVICE	NO. OF CHANNELS	PACKAGE LEADS						
		DBV	DCK	D	DSG	PW	DDF	
TSV911	1	5	5	—	—	—	—	
TSV912	2	—	—	8	8	—	8	
TSV914	4	—	—	14	—	14	—	



# 6 Pin Configuration and Functions



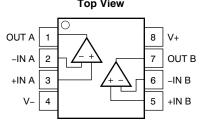


### Pin Functions: TSV911

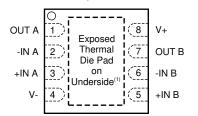
	PIN				
NAME	NO.			DESCRIPTION	
	DBV (SOT-23)	DCK (SC70)			
-IN	4	3	Ι	Inverting input	
+IN	3 1		Ι	Noninverting input	
OUT	1	4	0	Output	
V-	2	2	—	Negative (lowest) supply or ground (for single-supply operation)	
V+	5 5		—	Positive (highest) supply	



#### TSV912 D, DGK, DDF Packages 8-Pin SOIC, VSSOP Top View



#### TSV912 DSG Package (1) 8-Pin WSON With Exposed Thermal Pad Top View



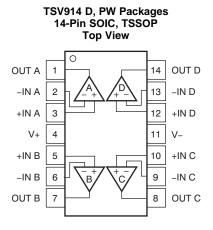
(1) Connect exposed thermal pad to V–. See *Packages with an Exposed Thermal Pad* section for more information.

#### Pin Functions: TSV912

PIN		I/O	DESCRIPTION		
NAME	NO.	1/0	DESCRIPTION		
–IN A	2	I	Inverting input, channel A		
+IN A	3	I	Noninverting input, channel A		
–IN B	6	I	Inverting input, channel B		
+IN B	5	I	Noninverting input, channel B		
OUT A	1	0	Output, channel A		
OUT B	7	0	Output, channel B		
V–	4	—	Negative (lowest) supply or ground (for single-supply operation)		
V+	8	—	Positive (highest) supply		

6





#### **Pin Functions: TSV914**

PIN		I/O	DESCRIPTION		
NAME	NO.	1/0	DESCRIPTION		
–IN A	2	I	Inverting input, channel A		
+IN A	3	I	Noninverting input, channel A		
–IN B	6	I	Inverting input, channel B		
+IN B	5	I	Noninverting input, channel B		
–IN C	9	I	Inverting input, channel C		
+IN C	10	I	Noninverting input, channel C		
–IN D	13	I	Inverting input, channel D		
+IN D	12	I	Noninverting input, channel D		
OUT A	1	0	Output, channel A		
OUT B	7	0	Output, channel B		
OUT C	8	0	Output, channel C		
OUT D	14	0	Output, channel D		
V–	11	—	Negative (lowest) supply or ground (for single-supply operation)		
V+	4	—	Positive (highest) supply		

## 7 Specifications

#### 7.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT	
Supply voltage			6	V		
	Voltage <sup>(2)</sup>	Common-mode	(V–) – 0.5	(V+) + 0.5	V	
Signal input pins	voltage -/	Differential		(V+) - (V-) + 0.2		
	Current <sup>(2)</sup>		-10	10	mA	
Output short-circuit <sup>(3)</sup>			Cont	inuous	mA	
Specified, T <sub>A</sub>		-40	125	°C		
Junction, T <sub>J</sub>				150	°C	
Storage, T <sub>stg</sub>			-65	150	°C	

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Input pins are diode-clamped to the power-supply rails. Current limit input signals that can swing more than 0.5 V beyond the supply rails to 10 mA or less.

(3) Short-circuit to ground, one amplifier per package.

## 7.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted)

			VALUE	UNIT
V	Electrostatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±4000	V
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

#### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_{S}$	Supply voltage	2.5	5.5	V
	Specified temperature	-40	125	°C

#### 7.4 Thermal Information: TSV911

		TSV	911	
	THERMAL METRIC <sup>(1)</sup>	DBV (SOT-23)	DCK (SC70)	UNIT
		5 PINS	5 PINS	
$R_{\thetaJA}$	Junction-to-ambient thermal resistance	221.7	263.3	°C/W
R <sub>0JC(top)</sub>	Junction-to-case(top) thermal resistance	144.7	75.5	°C/W
$R_{\thetaJB}$	Junction-to-board thermal resistance	49.7	51.0	°C/W
ΨJT	Junction-to-top characterization parameter	26.1	1.0	°C/W
ΨЈВ	Junction-to-board characterization parameter	49.0	50.3	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 7.5 Thermal Information: TSV912

			TSVS	912		
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	DGK (VSSOP)	DSG (WSON)	DDF (SOT-23)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\thetaJA}$	Junction-to-ambient thermal resistance	157.6	201.2	94.4	184.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	104.6	85.7	116.5	112.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	99.7	122.9	61.3	99.9	°C/W
ΨJT	Junction-to-top characterization parameter	55.6	21.2	13	18.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	99.2	121.4	61.7	99.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	N/A	N/A	34.4	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## 7.6 Thermal Information: TSV914

			TSV914	
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	PW (TSSOP)	UNIT
		14 PINS	14 PINS	
$R_{\thetaJA}$	Junction-to-ambient thermal resistance	106.9	205.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	69	106.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	63	133.9	°C/W
ΨJT	Junction-to-top characterization parameter	25.9	34.4	°C/W
ΨЈВ	Junction-to-board characterization parameter	62.7	132.6	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

# 7.7 Electrical Characteristics: $V_s$ (Total Supply Voltage) = (V+) – (V–) = 2.5 V to 5.5 V

at  $T_A = 25^{\circ}$ C,  $R_L = 10 \text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE					
		V <sub>S</sub> = 5 V		±0.3	±1.5	
V <sub>OS</sub>	Input offset voltage	$V_S = 5 V$ $T_A = -40^{\circ}C$ to 125°C			±3	mV
dV <sub>OS</sub> /dT	Drift	$V_S = 5 V$ $T_A = -40^{\circ}C \text{ to } 125^{\circ}C$		±0.5		µV/°C
PSRR	Power-supply rejection ratio	$V_{S} = 2.5 V - 5.5 V, V_{CM} = (V-)$		±7		μV/V
	Channel separation, DC	At DC		100		dB
INPUT VO	OLTAGE RANGE		I		4	
V <sub>CM</sub>	Common-mode voltage range	$V_{\rm S} = 2.5 \text{ V to } 5.5 \text{ V}$	(V–) – 0.1		(V+) + 0.1	V
		$ \begin{array}{l} V_S = 5.5 \ V \\ (V-) & - 0.1 \ V < V_{CM} < (V+) - 1.4 \ V \\ T_A = -40^\circ C \ to \ 125^\circ C \end{array} $	80	103		
CMRR	Common-mode rejection ratio	$V_{S} = 5.5 \text{ V}, V_{CM} = -0.1 \text{ V} \text{ to } 5.6 \text{ V}$ $T_{A} = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	57	87		dB
		$V_{S} = 2.5 \text{ V}, (V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V}$ $T_{A} = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$		88		
		$V_{S} = 2.5 \text{ V}, V_{CM} = -0.1 \text{ V} \text{ to } 1.9 \text{ V}$ $T_{A} = -40^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$		81		
INPUT BI	AS CURRENT	•			ł	
I <sub>B</sub>	Input bias current			±1		pА
I <sub>OS</sub>	Input offset current			±0.05		pА
NOISE		·			1	
En	Input voltage noise (peak-to-peak)	$V_{\rm S} = 5 \text{ V}, \text{ f} = 0.1 \text{ Hz to } 10 \text{ Hz}$		4.77		μV <sub>PP</sub>
		V <sub>S</sub> = 5 V, f = 10 kHz		12		<u>, , , , , , , , , , , , , , , , , , , </u>
e <sub>n</sub>	Input voltage noise density	V <sub>S</sub> = 5 V, f = 1 kHz		18		nV/√H
i <sub>n</sub>	Input current noise density	f = 1 kHz		10		fA/√H
INPUT C	APACITANCE					
C <sub>ID</sub>	Differential			2		pF
CIC	Common-mode			4		pF
OPEN-LC	DOP GAIN					
		$V_{S}$ = 2.5 V, (V–) + 0.04 V < $V_{O}$ < (V+) – 0.04 V $R_{L}$ = 10 k $\Omega$		100		
Δ	Open-loop voltage gain		104	130		dB
A <sub>OL</sub>	Open-loop voltage gain			100		uВ
		$V_{S}$ = 5.5 V, (V–) + 0.15 V < $V_{O}$ < (V+) – 0.15 V $R_{L}$ = 2 $k\Omega$		130		
FREQUE	NCY RESPONSE					
GBP	Gain bandwidth product	V <sub>S</sub> = 5 V, G = 1		8		MHz
φ <sub>m</sub>	Phase margin	V <sub>S</sub> = 5 V, G = 1		55		٥
SR	Slew rate	$ \begin{array}{l} V_S=5 \; V, \; G=1 \\ R_L=2 \; k\Omega \\ C_L=100 \; p F \end{array} $		4.5		V/µs
to	Settling time	To 0.1%, $V_S$ = 5 V, 2-V step , G = 1 $C_L$ = 100 pF		0.5		μs
t <sub>S</sub>		To 0.01%, $V_S$ = 5 V, 2-V step , G = 1 $C_L$ = 100 pF		1		μə
t <sub>OR</sub>	Overload recovery time	$V_{S} = 5 V, V_{IN} \times gain > V_{S}$		0.2		μs
THD + N	Total harmonic distortion + noise <sup>(1)</sup>	$V_{S} = 5 V, V_{O} = 1 V_{RMS}, G = 1, f = 1 \text{ kHz}$		0.0008%		
OUTPUT						
Vo	Voltage output swing from supply	$V_{S} = 5.5 \text{ V}, \text{ R}_{L} = 10 \text{ k}\Omega$			15	mV
•0	rails	$V_{\rm S} = 5.5 \text{ V}, \text{ R}_{\rm L} = 2 \text{ k}\Omega$			50	1117

(1) Third-order filter; bandwidth = 80 kHz at - 3 dB.



# Electrical Characteristics: $V_s$ (Total Supply Voltage) = (V+) – (V–) = 2.5 V to 5.5 V (continued)

at  $T_A = 25^{\circ}$ C,  $R_L = 10 \text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)

				,		
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I <sub>SC</sub>	Short-circuit current	V <sub>S</sub> = 5 V		±50		mA
Zo	Open-loop output impedance	V <sub>S</sub> = 5 V, f = 10 MHz		100		Ω
POWEF	R SUPPLY					
		$V_{S} = 5.5 \text{ V}, I_{O} = 0 \text{ mA}$		550	750	
IQ	Quiescent current per amplifier	$V_{\rm S}$ = 5.5 V, $I_{\rm O}$ = 0 mA $T_{\rm A}$ = -40°C to 125°C			1100	μΑ

TSV911, TSV912, TSV914

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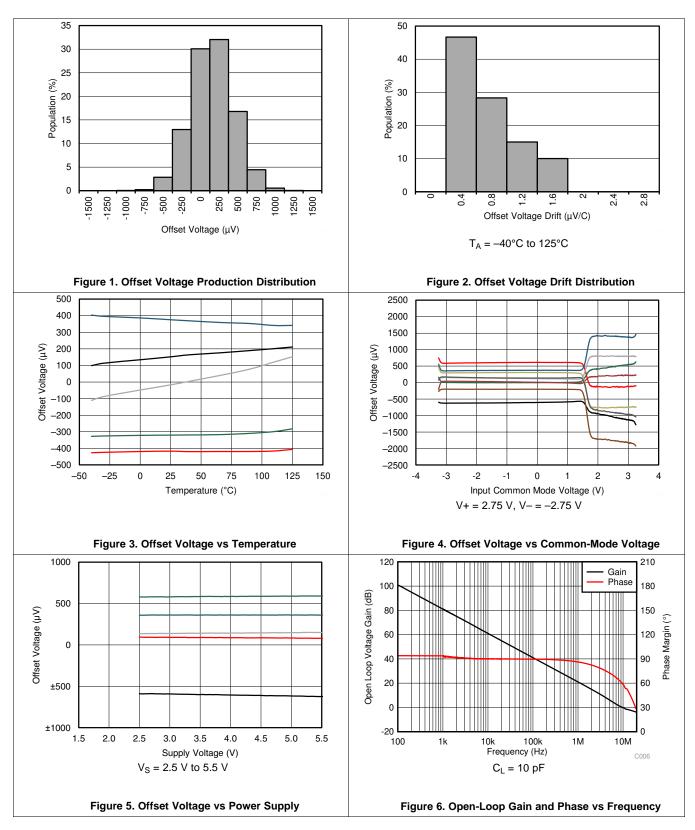
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### 7.8 Typical Characteristics

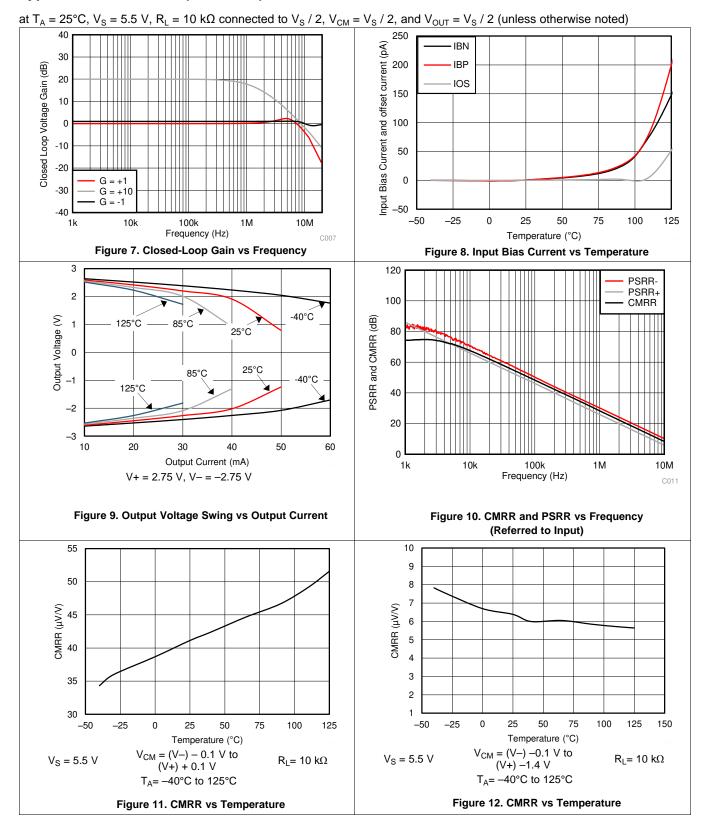
at  $T_A = 25^{\circ}C$ ,  $V_S = 5.5$  V,  $R_L = 10$  k $\Omega$  connected to  $V_S$  / 2,  $V_{CM} = V_S$  / 2, and  $V_{OUT} = V_S$  / 2 (unless otherwise noted)



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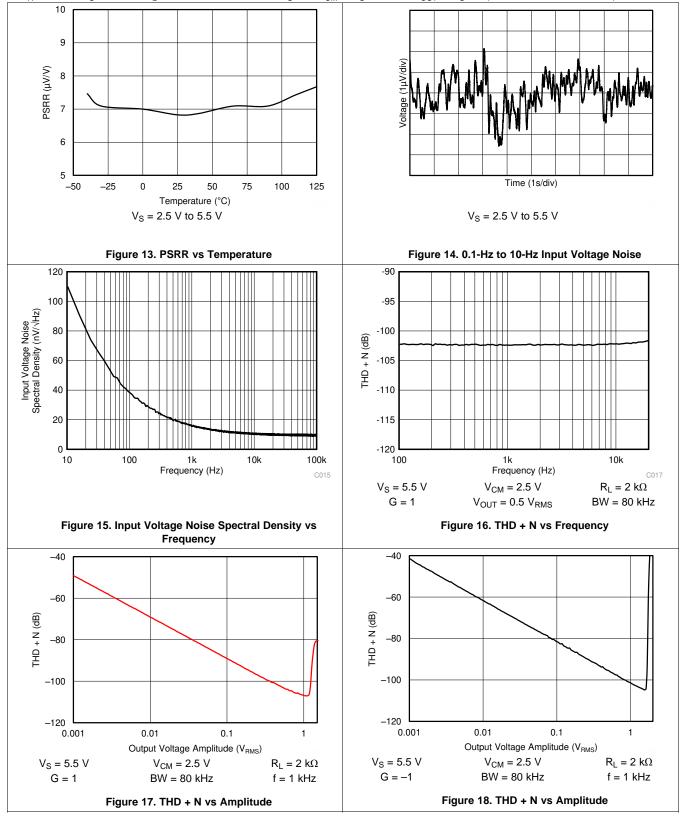
#### **Typical Characteristics (continued)**



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## **Typical Characteristics (continued)**

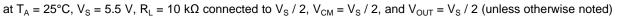
at  $T_A = 25^{\circ}$ C,  $V_S = 5.5$  V,  $R_L = 10$  k $\Omega$  connected to  $V_S$  / 2,  $V_{CM} = V_S$  / 2, and  $V_{OUT} = V_S$  / 2 (unless otherwise noted)

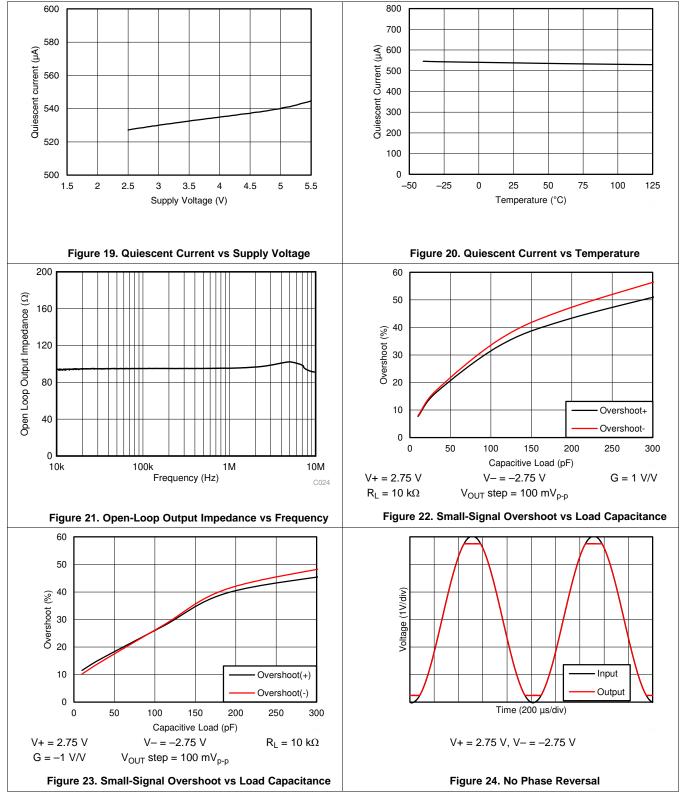


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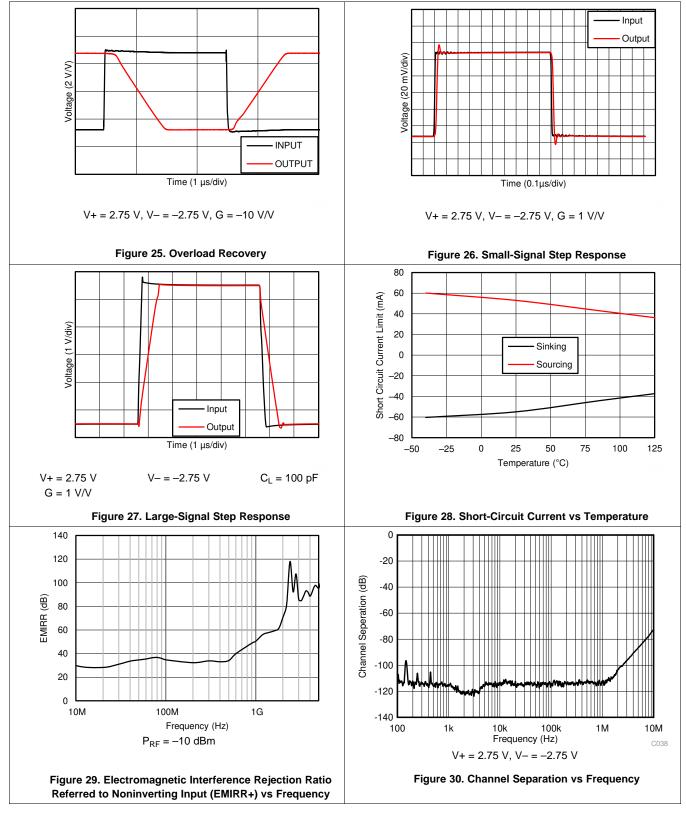
#### **Typical Characteristics (continued)**





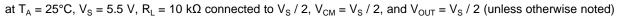
## **Typical Characteristics (continued)**

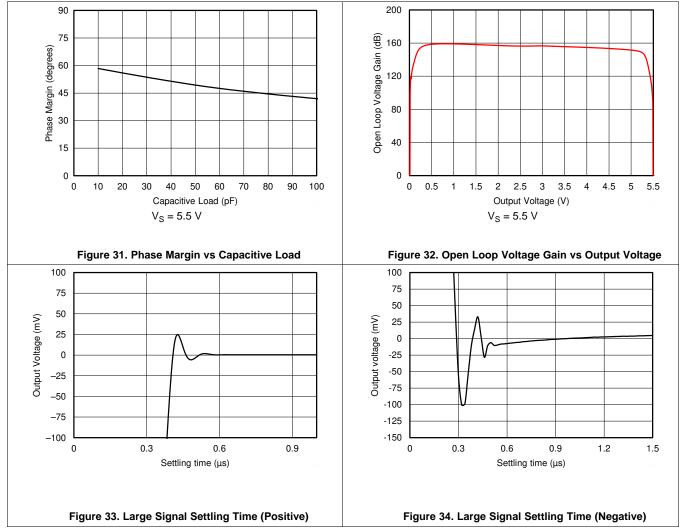
at  $T_A = 25^{\circ}$ C,  $V_S = 5.5$  V,  $R_L = 10$  k $\Omega$  connected to  $V_S$  / 2,  $V_{CM} = V_S$  / 2, and  $V_{OUT} = V_S$  / 2 (unless otherwise noted)





#### **Typical Characteristics (continued)**



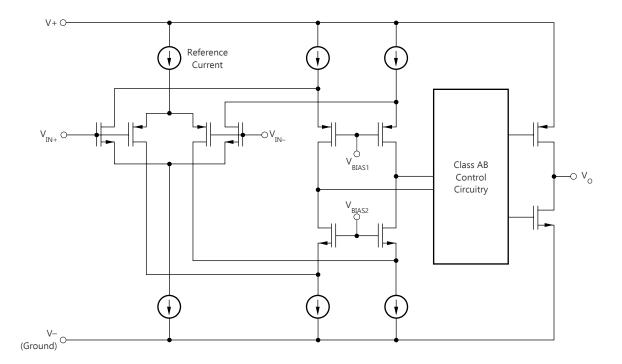


## 8 Detailed Description

#### 8.1 Overview

The TSV91x series is a family of low-power, rail-to-rail input and output op amps. These devices operate from 2.5 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes both rails and allows the TSV91x series to be used in virtually any single-supply application. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications and are designed for driving sampling analog-to-digital converters (ADCs).

### 8.2 Functional Block Diagram





#### 8.3 Feature Description

The input common-mode voltage range of the TSV91x family extends 100 mV beyond the supply rails for the full supply voltage range of 2.5 V to 5.5 V. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the *Functional Block Diagram*. The N-channel pair is active for input voltages close to the positive rail, typically (V+) - 1.4 V to 100 mV above the positive supply, whereas the P-channel pair is active for inputs from 100 mV below the negative supply to approximately (V+) - 1.4 V. There is a small transition region, typically (V+) - 1.2 V to (V+) - 1 V, in which both pairs are on. This 200-mV transition region can vary up to 200 mV with process variation. Thus, the transition region (with both stages on) can range from (V+) - 1.4 V to (V+) - 1.2 V on the low end, and up to (V+) - 1 V to (V+) - 0.8 V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD can degrade compared to device operation outside this region.

#### 8.3.2 Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the TSV91x series delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of 10 k $\Omega$ , the output swings to within 15 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

#### 8.3.3 Packages with an Exposed Thermal Pad

The TSV91x family is available in packages such as the WSON-8 (DSG) which feature an exposed thermal pad. Inside the package, the die is attached to this thermal pad using an electrically conductive compound. For this reason, when using a package with an exposed thermal pad, the thermal pad must either be connected to V– or left floating. Attaching the thermal pad to a potential other then V– is not allowed, and the performance of the device is not assured when doing so.

#### 8.3.4 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return to the linear state. After the charge carriers return to the linear state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the TSV91x series is approximately 200 ns.

#### 8.4 Device Functional Modes

The TSV91x family has a single functional mode. These devices are powered on as long as the power-supply voltage is between 2.5 V ( $\pm$ 1.25 V) and 5.5 V ( $\pm$ 2.75 V).



### 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The TSV91x series features 8-MHz bandwidth and 4.5-V/ $\mu$ s slew rate with only 550  $\mu$ A of supply current per channel, providing good AC performance at low power consumption. DC applications are well served with a low input noise voltage of 18 nV /  $\sqrt{Hz}$  at 1 kHz, low input bias current, and a typical input offset voltage of 0.3 mV.

#### 9.2 Typical Application

Figure 35 shows the TSV91x configured in a low-side, motor-control application.

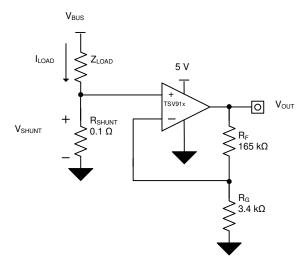


Figure 35. TSV91x in a Low-Side, Motor-Control Application

#### 9.2.1 Design Requirements

The design requirements for this design are:

- Load current: 0 A to 1 A
- Output voltage: 4.95 V
- Maximum shunt voltage: 100 mV



#### Typical Application (continued)

#### 9.2.2 Detailed Design Procedure

The transfer function of the circuit in Figure 35 is shown in Equation 1.

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain$$

The load current (I<sub>LOAD</sub>) produces a voltage drop across the shunt resistor (R<sub>SHUNT</sub>). The load current is set from 0 A to 1 A. To keep the shunt voltage below 100 mV at maximum load current, the largest shunt resistor is defined using Equation 2.

$$R_{SHUNT} = \frac{V_{SHUNT} MAX}{I_{LOAD} MAX} = \frac{100 \text{mV}}{1 \text{A}} = 100 \text{m}\Omega$$
(2)

Using Equation 2, R<sub>SHUNT</sub> is 100 mΩ. The voltage drop produced by I<sub>LOAD</sub> and R<sub>SHUNT</sub> is amplified by the TSV91x to produce an output voltage of approximately 0 V to 4.95 V. The gain required by the TSV91x to produce the necessary output voltage is calculated using Equation 3:

$$Gain = \frac{\left(V_{OUT\_MAX} - V_{OUT\_MIN}\right)}{\left(V_{IN\_MAX} - V_{IN\_MIN}\right)}$$
(3)

Using Equation 3, the required gain is calculated to be 49.5 V/V, which is set with resistors R<sub>F</sub> and R<sub>G</sub>. Equation 4 is used to size the resistors,  $R_F$  and  $R_G$ , to set the gain of the TSV91x to 49.5 V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)}$$
(4)

Selecting R<sub>F</sub> as 165 k $\Omega$  and R<sub>G</sub> as 3.4 k $\Omega$  provides a combination that equals roughly 49.5 V/V. Figure 36 shows the measured transfer function of the circuit shown in Figure 35.

#### 9.2.3 Application Curve

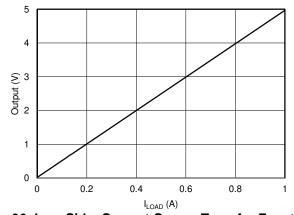


Figure 36. Low-Side, Current-Sense, Transfer Function

(1)



### **10 Power Supply Recommendations**

The TSV91x series is specified for operation from 2.5 V to 5.5 V ( $\pm$ 1.25 V to  $\pm$ 2.75 V); many specifications apply from –40°C to 125°C. The *Typical Characteristics* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

#### CAUTION

Supply voltages larger than 6 V can permanently damage the device; see the *Absolute Maximum Ratings* table.

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or highimpedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout Example* section.

#### **10.1** Input and ESD Protection

The TSV91x series incorporates internal ESD protection circuits on all pins. For input and output pins, this protection consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10-mA, as stated in the *Absolute Maximum Ratings* table. Figure 37 shows how a series input resistor is added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

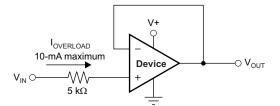


Figure 37. Input Current Protection



## 11 Layout

#### 11.1 Layout Guidelines

For best operational performance of the device, use good printed-circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and of op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in Figure 39, keeping RF and RG close to the inverting input minimizes parasitic capacitance on the inverting input.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

#### 11.2 Layout Example

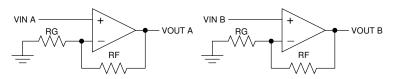
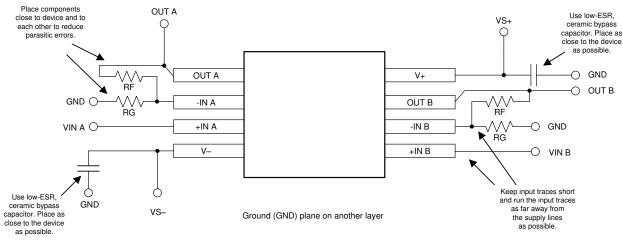
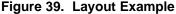


Figure 38. Schematic Representation for Figure 39





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## **12 Device and Documentation Support**

#### **12.1** Documentation Support

#### 12.1.1 Related Documentation

For related documentation see the following:

Texas Instruments, Circuit Board Layout Techniques, SLOA089

#### 12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

PARTS	PRODUCT FOLDER ORDER NOW		TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TSV911	Click here	Click here	Click here	Click here	Click here
TSV912	Click here	Click here	Click here	Click here	Click here
TSV914	Click here	Click here	Click here	Click here	Click here

#### Table 1. Related Links

#### 12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 12.4 Community Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 12.5 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### **12.6 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 12.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TSV911AIDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	(6) NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	1U2F	
											Samples
TSV911AIDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	1EK	Samples
TSV912AIDDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T12A	Samples
TSV912AIDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG   SN	Level-2-260C-1 YEAR	-40 to 125	T912	Samples
TSV912AIDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAUAG   SN	Level-2-260C-1 YEAR	-40 to 125	T912	Samples
TSV912AIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 125	TSV912	Samples
TSV912AIDSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T912	Samples
TSV912AIDSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T912	Samples
TSV912AIPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 125	TSV912	Samples
TSV914AIDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TSV914AD	Samples
TSV914AIPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TSV914	Samples
TSV914AIPWT	ACTIVE	TSSOP	PW	14	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	TSV914	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.



# PACKAGE OPTION ADDENDUM

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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NSTRUMENTS

## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TSV911AIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV911AIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV911AIDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TSV912AIDDFR	SOT-23- THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV912AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TSV912AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TSV912AIDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TSV912AIDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TSV912AIDR	SOIC	D	8	2500	330.0	15.4	6.4	5.2	2.1	8.0	12.0	Q1
TSV912AIDSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TSV912AIDSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TSV912AIPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TSV912AIPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TSV914AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TSV914AIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



9-Aug-2022

Ĩ	Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	TSV914AIPWT	TSSOP	PW	14	250	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



# PACKAGE MATERIALS INFORMATION

9-Aug-2022



All dimensions are nominal			<b>D</b> :	0.50			
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TSV911AIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TSV911AIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TSV911AIDCKR	SC70	DCK	5	3000	190.0	190.0	30.0
TSV912AIDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TSV912AIDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
TSV912AIDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
TSV912AIDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
TSV912AIDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
TSV912AIDR	SOIC	D	8	2500	333.2	345.9	28.6
TSV912AIDSGR	WSON	DSG	8	3000	210.0	185.0	35.0
TSV912AIDSGT	WSON	DSG	8	250	210.0	185.0	35.0
TSV912AIPWR	TSSOP	PW	8	2000	356.0	356.0	35.0
TSV912AIPWR	TSSOP	PW	8	2000	366.0	364.0	50.0
TSV914AIDR	SOIC	D	14	2500	356.0	356.0	35.0
TSV914AIPWR	TSSOP	PW	14	2000	366.0	364.0	50.0
TSV914AIPWT	TSSOP	PW	14	250	366.0	364.0	50.0

# **DBV0005A**



# **PACKAGE OUTLINE**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. Refernce JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.



# DBV0005A

# **EXAMPLE BOARD LAYOUT**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DBV0005A

# **EXAMPLE STENCIL DESIGN**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

8. Board assembly site may have different recommendations for stencil design.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
   E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



A. An integration of the information o

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



## D0008A



## **PACKAGE OUTLINE**

#### SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



## D0008A

# **EXAMPLE BOARD LAYOUT**

#### SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



### D0008A

## **EXAMPLE STENCIL DESIGN**

### SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.

- D Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



## DGK (S-PDSO-G8)

### PLASTIC SMALL OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



## DSG 8

2 x 2, 0.5 mm pitch

## **GENERIC PACKAGE VIEW**

#### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





## DSG0008A



### **PACKAGE OUTLINE**

#### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



## DSG0008A

# **EXAMPLE BOARD LAYOUT**

#### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

 This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

 Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



## DSG0008A

## **EXAMPLE STENCIL DESIGN**

#### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



### **PW0008A**



### **PACKAGE OUTLINE**

#### TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



### PW0008A

# **EXAMPLE BOARD LAYOUT**

### TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



### PW0008A

## **EXAMPLE STENCIL DESIGN**

### TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



<sup>8.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES: A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - D. Falls within JEDEC MO-203 variation AA.



### LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



## **DDF0008A**



### **PACKAGE OUTLINE**

#### SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.



## **DDF0008A**

## **EXAMPLE BOARD LAYOUT**

### SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



4. Publication IPC-7351 may have alternate designs.

5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



### **DDF0008A**

## **EXAMPLE STENCIL DESIGN**

### SOT-23 - 1.1 mm max height

PLASTIC SMALL OUTLINE



6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

7. Board assembly site may have different recommendations for stencil design.



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